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Docket No. 0756-1914 11-15-02

Muller

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Shunpei YAMAZAKI et al.

Serial No. 09/235,770

Filed: January 25, 1999

For: SEMICONDUCTOR DEVICE

AND METHOD FOR FORMING

THE SAME

) Art Unit: 2813

) Examiner: L. Schillinger

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with The United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on 11/14/02

AMENDMENT

Honorable Commissioner of Patents

Washington, D.C. 20231

Sir:

In response to the Office Action dated June 4, 2002 please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 3, 6, 9, 13, 16 and 19 as follows:

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D¹ 3. (Amended) A semiconductor device according to claim 1 wherein a thickness of said first insulating film is 10-50 nm, a thickness of said second insulating film is 100-800 nm, a thickness of said third insulating film is 50-200 nm and a thickness of said fourth insulating film is 2-20 nm.

D² 6. (Amended) A semiconductor device according to claim 4 wherein a thickness of said first insulating film is 10-50 nm, a thickness of said second insulating film is 100-800 nm, a thickness of said third insulating film is 50-200 nm and a thickness of said fourth insulating film is 2-20 nm.

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